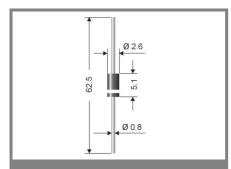
## 1N 4001...1N 4007, 1N 4007-1300



### **Axial lead diode**

# Standard silicon rectifier diodes

1N 4001...1N 4007, 1N 4007-1300

**Forward Current: 1 A** 

Reverse Voltage: 50 to 1300 V

#### **Features**

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0

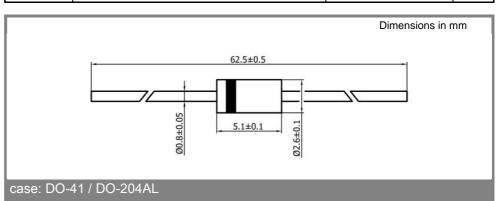
#### **Mechanical Data**

- Plastic case DO-41 / DO-204AL
- Weight approx.: 0.4 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 5000 pieces per ammo
- Valid, if leads are kept at ambient temperature at a distance of 10 mm from
- 2) I<sub>F</sub>=1A, T<sub>i</sub>=25°C
- 3) T<sub>A</sub> = 25 °C

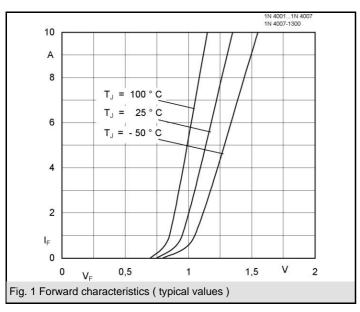
Туре	Repetitive peak reverse voltage	Surge peak reverse voltage	Max. reverse recovery time	Max. forward voltage
			I <sub>F</sub> = - A I <sub>R</sub> = - A I <sub>RR</sub> = - A	
	V <sub>RRM</sub> V	V <sub>RSM</sub> V	t <sub>rr</sub> ns	V <sub>F</sub> <sup>2)</sup>
1N 4001	50	50	-	1,1
1N 4002	100	100	-	1,1
1N 4003	200	200	-	1,1
1N 4004	400	400	-	1,1
1N 4005	600	600	-	1,1
1N 4006	800	800	-	1,1
1N 4007	1000	1000	-	1,1
1N 4007-1300	1300	1300	-	1,1

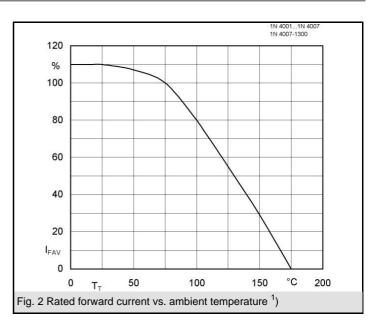
Absolute Maximum Ratings Tc = 25 °C unless otherwise specified					
Symbol	Conditions	Values	Units		
I <sub>FAV</sub>	Max. averaged fwd. current, R-load, T <sub>A</sub> = 75 °C <sup>1)</sup>	1	Α		
I <sub>FRM</sub>	Repetitive peak forward current f > 15 Hz <sup>1)</sup>	10	Α		
I <sub>FSM</sub>	Peak forward surge current 50 Hz half sinus-wave 3)	50	Α		
i²t	Rating for fusing, t < 10 ms <sup>3)</sup>	12,5	A²s		
R <sub>thA</sub>	Max. thermal resistance junction to ambient 1)	45	K/W		
R <sub>thT</sub>	Max. thermal resistance junction to terminals 1)	-	K/W		
T <sub>j</sub>	Operating junction temperature	-50+175	°C		
T <sub>s</sub>	Storage temperature	-50+175	°C		

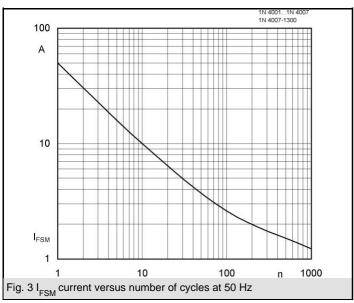
Characte	haracteristics Tc = 25 °C, unless otherwise sp		ecified
Symbol	Conditions	Values	Units
I <sub>R</sub>	Maximum leakage current, $T_j = 25 ^{\circ}\text{C}$ ; $V_R = V_{RRM}$	<5	μΑ
	$T_j = 100 ^{\circ}\text{C};  V_R = V_{RRM}$	<50	μA
СЈ	Typical junction capacitance (at MHz and applied reverse voltage of V)	-	pF
Q <sub>rr</sub>	Reverse recovery charge $(U_R = V; I_F = A; dI_F/dt = A/ms)$	-	μC
E <sub>RSM</sub>	Non repetitive peak reverse avalanche energy ( $I_R = mA$ ; $T_j = ^{\circ}C$ ; inductive load switched off)	-	mJ



# 1N 4001...1N 4007, 1N 4007-1300







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